All Bond Pads = 0.004" Sq. Substrate is also Gate.

At 25°C free air temperature:		NJ26 Process					
Static Electrical Characteristics		Min	Тур	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	V _{(BR)GSS}	- 30	- 40		V	$I_G = -1 \ \mu A, \ V_{DS} = \emptyset V$	
Reverse Gate Leakage Current	I _{GSS}		- 10	- 100	рА	$V_{GS} = -20 V$, $V_{DS} = \emptyset V$	
Drain Saturation Current (Pulsed)	I _{DSS}	2		22	mA	$V_{DS} = 15 V, V_{GS} = \emptyset V$	
Gate Source Cutoff Voltage	V _{GS(OFF)}	- 1		- 5	V	V _{DS} = 15V, I _D = 1 nA	
Dynamic Electrical Characteristics							
Forward Transconductance	9 _{fs}		6		mS	$V_{DS} = 15 V$, $V_{GS} = \emptyset V$	f = 1 kHz
Input Capacitance	C _{iss}		4.3	5.0	pF	$V_{DS} = 15 V, V_{GS} = \emptyset V$	f = 1 MHz
Feedback Capacitance	C _{rss}		1	1.5	pF	$V_{DS} = 15 V, V_{GS} = \emptyset V$	f = 1 MHz
Equivalent Noise Voltage	ē _N		4		nV/√HZ	V _{DS} = 10V, I _D = 5 mA	f = 1 kHz



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